

#### **Description**

The CSD17581Q5A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

DFN5X6-8L

N-Channel MOSFET

#### **General Features**

 $V_{DS} = 30 \text{ V} I_{D} = 120 \text{ A}$ 

 $R_{DS(ON)} < 4.4 \text{ m} \text{ V}_{GS}=10 \text{V}$ 

### **Application**

Battery protection

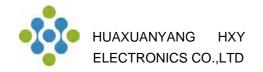
Load switch

## Uninterruptible power supply

Package Marking and Ordering Information					
Product ID	Pack	Brand	Qty(PCS)		
CSD17581Q5A	DFN5X6-8L	HXY MOSFET	5000		

Absolute Maximum Ratings (T<sub>C</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units	
Vps	Drain-Source Voltage	30	V	
Vgs	Gate-Source Voltage ±20		V	
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,6</sup>	А		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,6</sup>	66	А	
Ідм	Pulsed Drain Current <sup>2</sup> 320		А	
EAS	Single Pulse Avalanche Energy³	180	mJ	
las	Avalanche Current	60	А	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	187	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R <sub>θ</sub> JA	Thermal Resistance Junction-Ambient <sup>1</sup> 62		°C/W	
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	1.1	°C/W	



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
®BVoss/®TJ	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.014		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =30A		3.5	4.4	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		4.6	5.8	$\mathbf{m}\Omega$
V <sub>GS(th)</sub>	Gate Threshold Voltage	,	1.2		2.5	V
₹VGS(th)	V <sub>GS(th)</sub> Temperature Coefficient	── V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA		-4		mV/°C
Ipss		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
Igss	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =30A		50		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			56.9		
Qgs	Gate-Source Charge			13.8		nC
Qgd	Gate-Drain Charge			23.5		
Td(on)	Turn-On Delay Time			20.1		
Tr	Rise Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,		6.3		
Td(off)	Turn-Off Delay Time	—R <sub>G</sub> =3.3 , I <sub>D</sub> =1A		124.6		ns
T <sub>f</sub>	Fall Time			15.8		
Ciss	Input Capacitance			4345		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		340		pF
Crss	Reverse Transfer Capacitance			225		
Is	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			85	Α
VsD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V



## **Typical Characteristics**

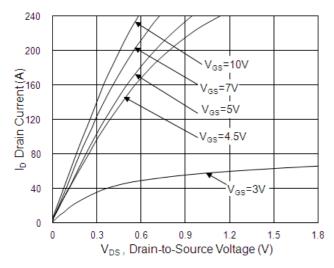


Fig.1 Typical Output Characteristics

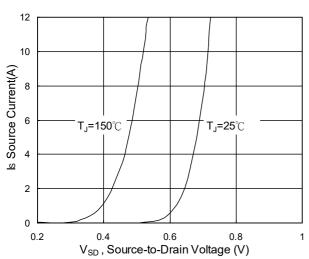


Fig.3 Forward Characteristics of Reverse

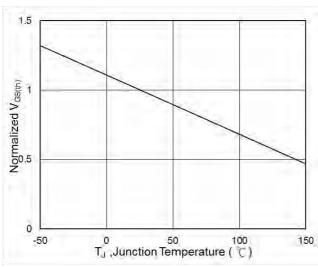


Fig.5 Normalized  $V_{\text{GS(th)}}$  v.s  $T_{\text{J}}$ 

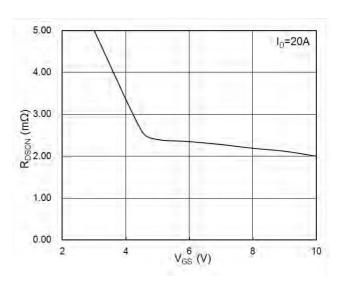


Fig.2 On-Resistance v.s Gate-Source

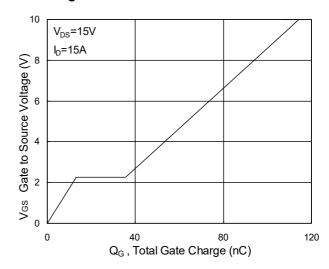


Fig.4 Gate-Charge Characteristics

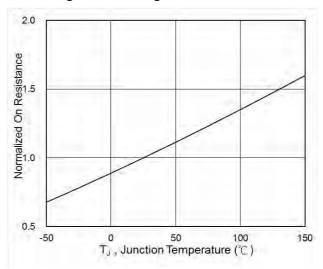


Fig.6 Normalized  $R_{DSON}$  v.s  $T_J$ 

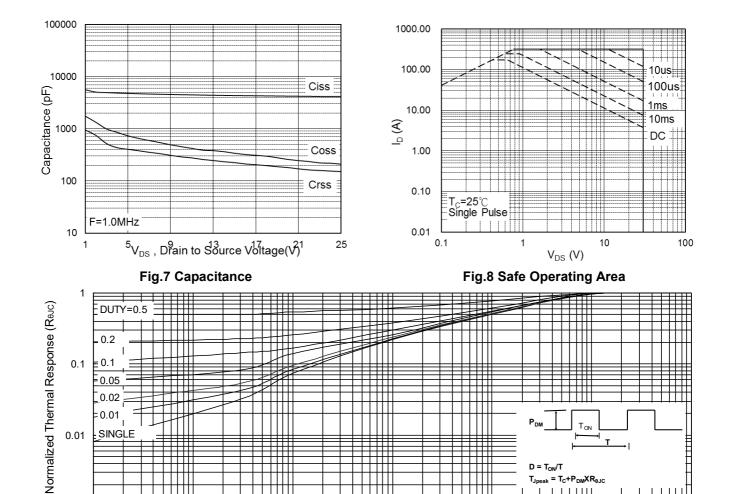
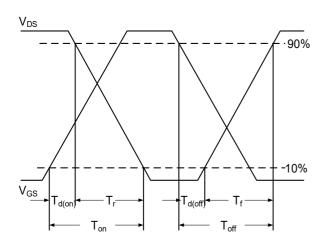


Fig.9 Normalized Maximum Transient Thermal Impedance

t, Pulse Width (s)

0.001



0.0001

0.0001

Fig.10 Switching Time Waveform

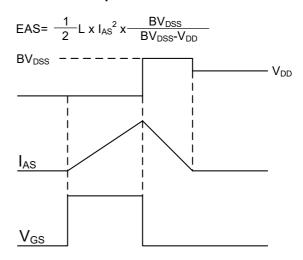
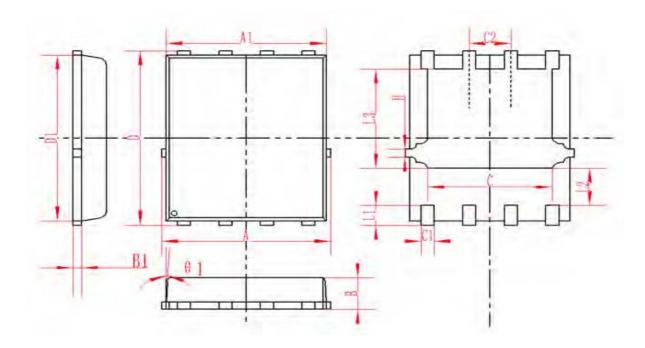


Fig.11 Unclamped Inductive Switching Waveform



# **DFN5X6-8L Package Information**



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
Α	5.3	5.5	5.7	0.208	0.216	0.224
A1	5.1	5.2	5.3	0.2	0.204	0.209
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.85	6.05	6.25	0.23	0.238	0.246
В	0.85	0.95	1.05	0.033	0.037	0.041
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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